ZXMP3A16G

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D max T_A = 25°C (Notes 3)
-30V	45mΩ @ V_{GS} = -10V	-7.5A
	70mΩ @ V_{GS} = -4.5V	-5.9A

Features and Benefits

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- **"Green" component. Lead Free Finish / RoHS compliant (Note 1)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

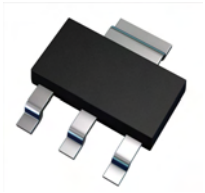
This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- DC-DC Converters
- Power management functions
- Relay and solenoid driving

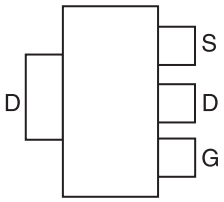
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (approximate)

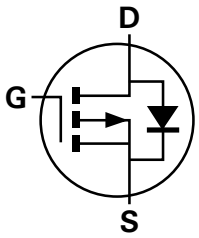
SOT223



Top View



Pin Out - Top View



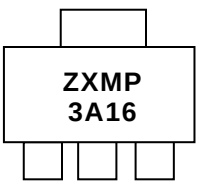
Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP3A16GTA	ZXMP3A16	7	12	1,000
ZXMP3A16GTC	ZXMP3A16	13	12	4,000

Note: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds. All applicable RoHS exemptions applied. Further information about Diodes Inc.'s "Green" Policy can be found on our website.

Marking Information



ZXMP = Product Type Marking Code, Line 1
3A16 = Product Type Marking Code, Line 2

Maximum Ratings @T_A = 25°C unless otherwise specified

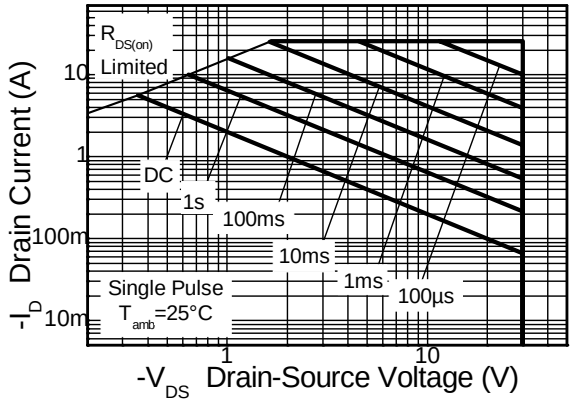
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	-30	V
Gate-Source voltage			V_{GS}	±20	V
Continuous Drain current	V_{GS} = 10V	(Note 3)	I_D	-7.5	A
		T_A = 70°C (Note 3)		-6.0	
		(Note 2)		-5.4	
Pulsed Drain current	V_{GS} = 10V	(Note 4)	I_{DM}	-24.9	A
Continuous Source current (Body diode)		(Note 3)	I_S	-3.2	A
Pulsed Source current (Body diode)		(Note 4)	I_{SM}	-24.9	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

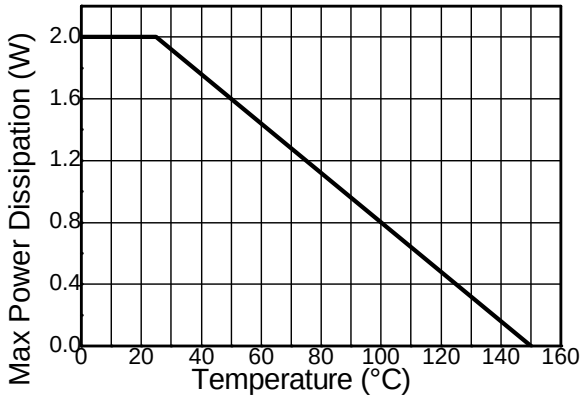
Characteristic		Symbol	Value	Unit
Power dissipation	(Note 2)	P_D	2.0	W
Linear derating factor			16	mW/°C
	(Note 3)		3.9	W
			31	mW/°C
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	62.5	°C/W
	(Note 3)		32.2	
Thermal Resistance, Junction to Lead	(Note 5)	$R_{\theta JL}$	8.51	
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	°C

Notes:
2. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
3. Same as note (2), except the device is measured at t ≤ 10 sec.
4. Same as note (2), except the device is pulsed with D= 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.
5. Thermal resistance from junction to solder-point (at the end of the drain lead).

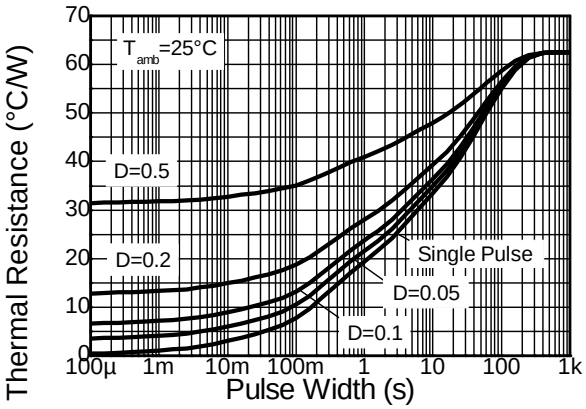
Thermal Characteristics



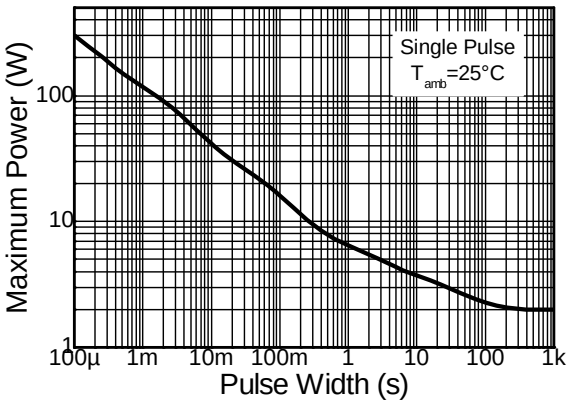
Safe Operating Area



Derating Curve



Transient Thermal Impedance



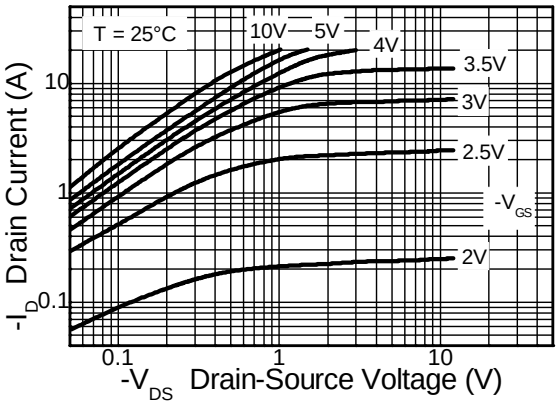
Pulse Power Dissipation

Electrical Characteristics @T_A = 25°C unless otherwise specified

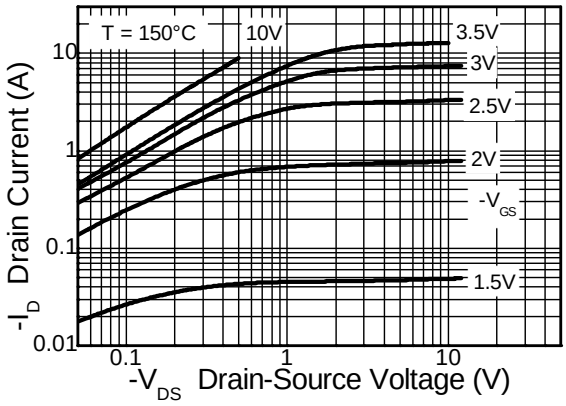
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	I_D = -250μA, V_{GS} = 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	—	V	I_D = -250μA, V_{DS} = V_{GS}
Static Drain-Source On-Resistance (Note 6)	$R_{DS\ (ON)}$	—	—	45	mΩ	V_{GS} = -10V, I_D = -4.2A
				70		V_{GS} = -4.5V, I_D = -3.4A
Forward Transconductance (Notes 6 & 7)	g_{fs}	—	9.2	—	S	V_{DS} = -15V, I_D = -4.2A
Diode Forward Voltage (Note 6)	V_{SD}	—	-0.85	-0.95	V	I_S = -3.6A, V_{GS} = 0V, T_J = 25°C
Reverse recovery time (Note 7)	t_{rr}		21.7	—	ns	I_F = -2A, di/dt = 100A/μs, T_J = 25°C
Reverse recovery charge (Note 7)	Q_{rr}	—	16.1	—	nC	
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	1022	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	267	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	229	—	pF	
Total Gate Charge (Note 8)	Q_g	—	17.2	—	nC	V_{GS} = -5V; V_{DS} = -15V, I_D = -4.2A
Total Gate Charge (Note 8)	Q_g	—	29.6	—	nC	V_{GS} = -10V; V_{DS} = -15V, I_D = -4.2A
Gate-Source Charge (Note 8)	Q_{gs}	—	2.8	—	nC	
Gate-Drain Charge (Note 8)	Q_{gd}	—	8.6	—	nC	
Turn-On Delay Time (Note 8)	$t_{D(on)}$	—	3.8	—	ns	V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 8)	t_r	—	6.5	—	ns	
Turn-Off Delay Time (Note 8)	$t_{D(off)}$	—	37.1	—	ns	
Turn-Off Fall Time (Note 8)	t_f	—	21.4	—	ns	

Notes:
6. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
7. For design aid only, not subject to production testing.
8. Switching characteristics are independent of operating junction temperatures.

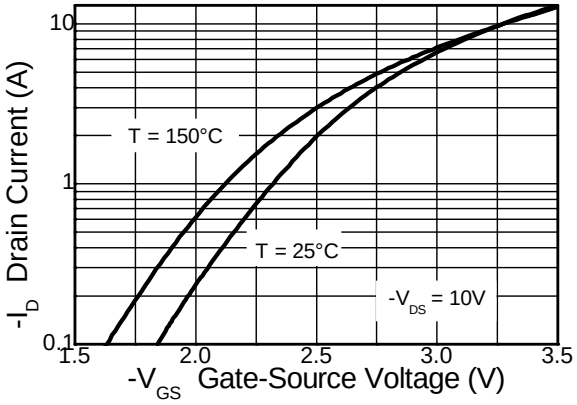
Typical Characteristics



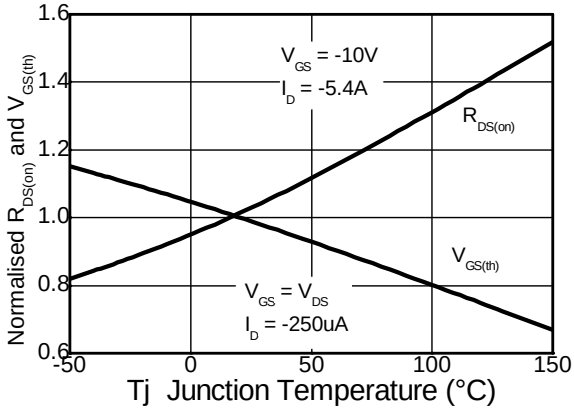
Output Characteristics



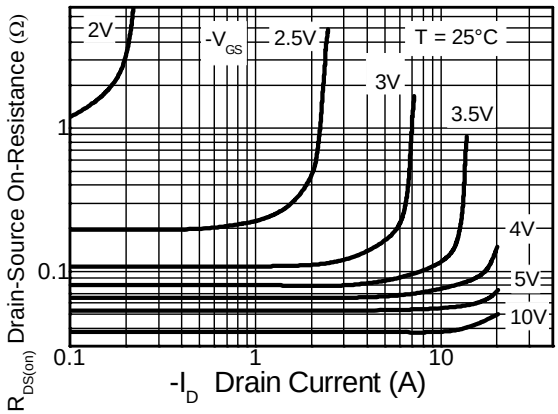
Output Characteristics



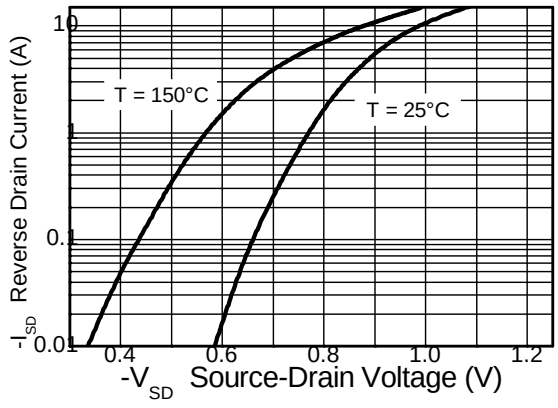
Typical Transfer Characteristics



Normalised Curves v Temperature

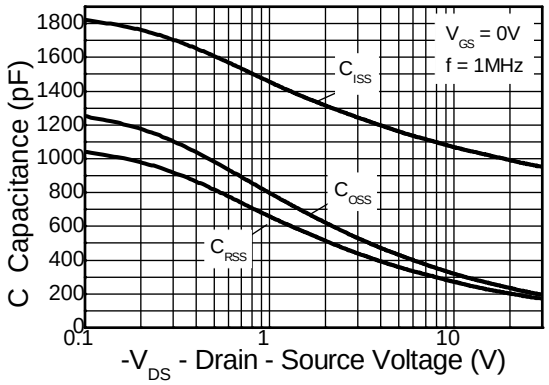


On-Resistance v Drain Current

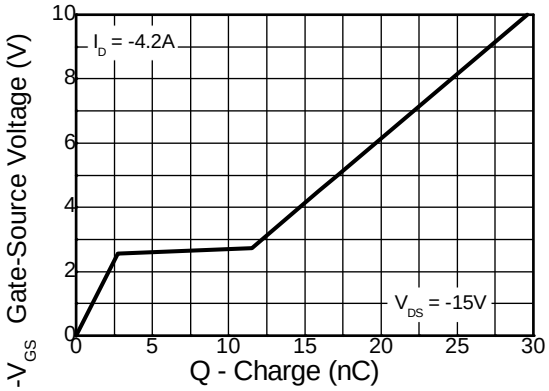


Source-Drain Diode Forward Voltage

Typical Characteristics – continued

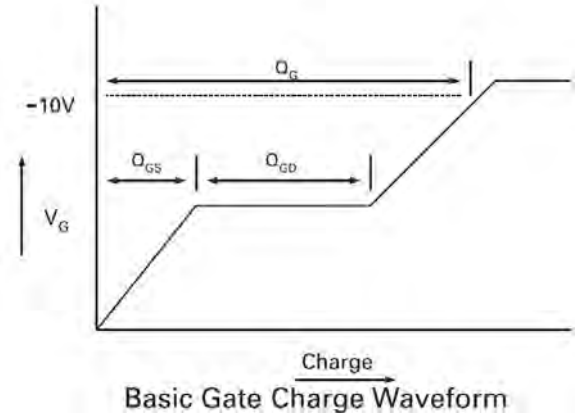


Capacitance v Drain-Source Voltage

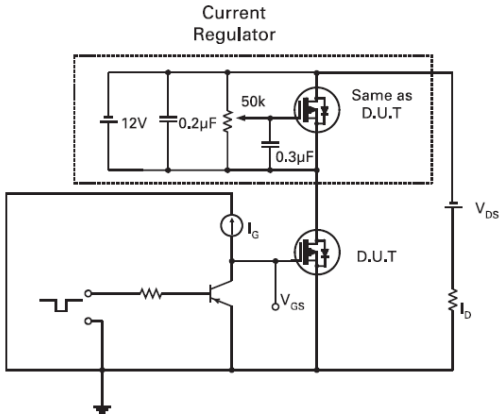


Gate-Source Voltage v Gate Charge

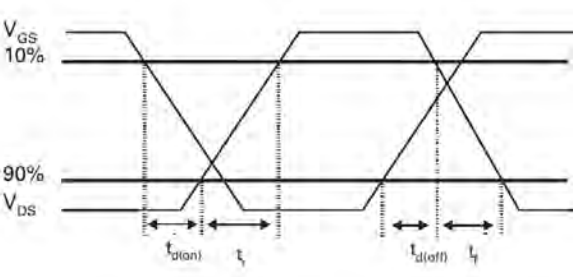
Test Circuits



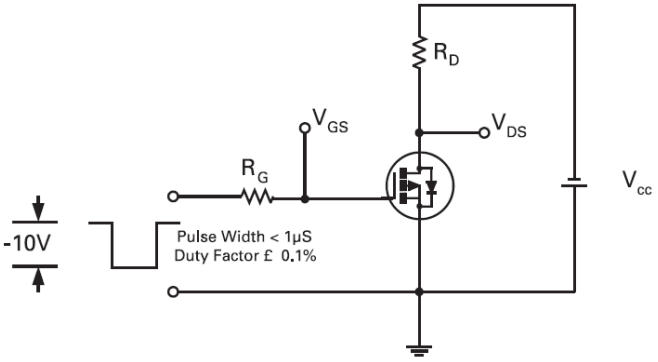
Basic Gate Charge Waveform



Gate Charge Test Circuit

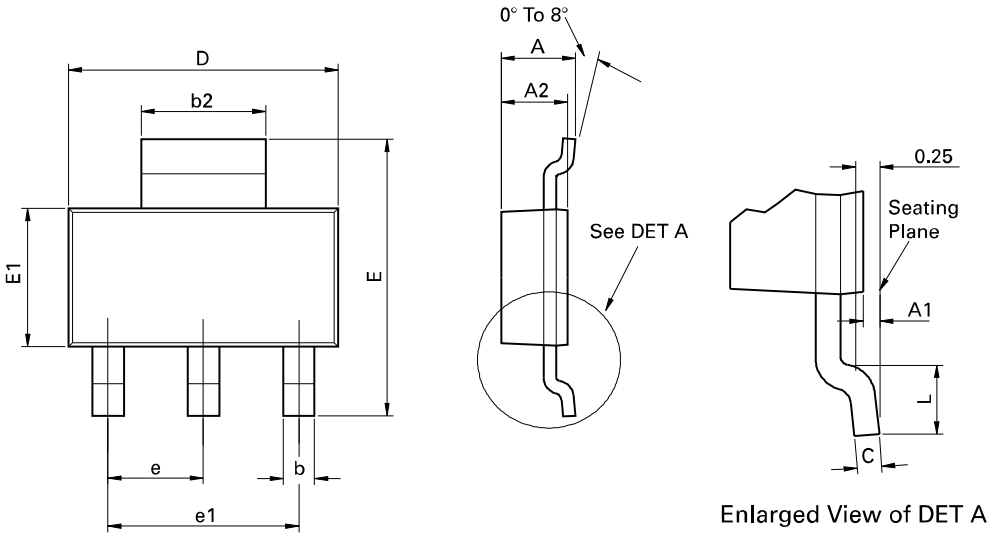


Switching Time Waveforms



Switching Time Test Circuit

Package Outline Dimensions



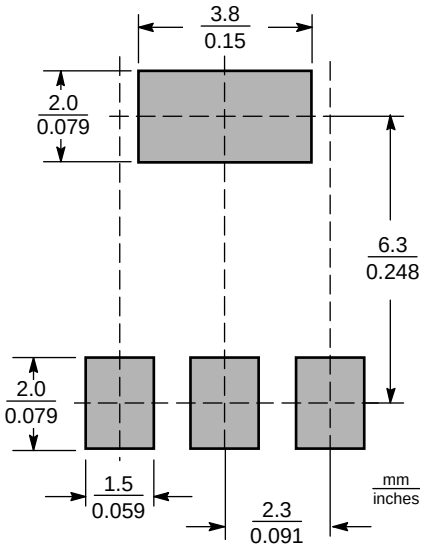
Enlarged View of DET A

Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	e	2.30 BSC		0.0905 BSC	
A2	1.55	1.65	0.0610	0.0649	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches.

Suggested Pad Layout



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